WHAT IS CLAIMED IS:

1. A method for providing a uniform oxide layer over a metal layer in a semiconductor device, said method comprising the steps of:

placing a layer of boron doped oxide over said metal layer;

placing a layer of phosphorus doped oxide over said layer of boron doped oxide;

calculating a time period required for a wet etch process to etch through said layer of phosphorus doped oxide; and

performing said wet etch process on said phosphorus doped oxide layer for said time period.

2. The method as set forth in Claim 1 wherein said metal layer in said semiconductor device is a metal link layer of a laser trimmed fuse.

3. The method as set forth in Claim 1 wherein said step of placing said layer of boron doped oxide over said metal layer comprises the step of:

forming said boron doped oxide layer with a desired thickness.

4. The method as set forth in Claim 3 wherein said desired thickness of said boron doped oxide layer is approximately five thousand Ångstroms.

5. The method as set forth in Claim 1 wherein said step of calculating said time period required for said wet etch process to etch through said layer of phosphorus doped oxide comprises the step of:

dividing a thickness of said phosphorus doped oxide layer by a value of an etch rate of said wet etch process through said phosphorus doped oxide layer.

6. The method as set forth in Claim 1 wherein said step of placing said layer of phosphorus doped oxide over said layer of boron doped oxide comprises the step of:

forming said phosphorus doped oxide layer with a desired thickness.

7. The method as set forth in Claim 6 wherein said desired thickness of said phosphorus doped oxide layer is approximately five thousand Ångstroms.

8. The method as set forth in Claim 1 further comprising the step of:

performing said wet etch process on said boron doped oxide layer after said wet etch process has etched through said phosphorus doped oxide layer; and

stopping said wet etch process after said wet etch process has begun to etch said boron doped oxide layer.

9. The method as set forth in claim 1 further comprising the steps of:

calculating a length of time required for said wet etch process to etch down to a desired thickness of said layer of boron doped oxide; and

performing said wet etch process on said boron doped oxide layer for said length of time after said wet etch process has etched through said phosphorus doped oxide layer.

10. The method as set forth in Claim 9 wherein said desired thickness of said boron doped oxide layer is approximately five thousand Ångstroms.

11. An apparatus for providing a uniform oxide layer over a metal layer in a semiconductor device, said apparatus comprising:

a semiconductor device comprising a metal layer;

a layer of boron doped oxide placed over said metal layer; and

a layer of phosphorus doped oxide placed over said layer of boron doped oxide.

12. The apparatus as set forth in Claim 11 wherein said metal layer in said semiconductor device is a metal link layer of a laser trimmed fuse.

13. The apparatus as set forth in Claim 11 wherein said layer of boron doped oxide is formed having a desired thickness.

14. The apparatus as set forth in Claim 13 wherein said desired thickness of said boron doped oxide is approximately five thousand Ångstroms.

15. The apparatus as set forth in Claim 11, wherein said layer of phosphorus doped oxide placed over said layer of phosphorus doped oxide is etched through down to said layer of boron doped oxide.

16. The apparatus as set forth in Claim 11 wherein said layer of phosphorus doped oxide is formed having a desired thickness.

17. The apparatus as set forth in Claim 16 wherein said desired thickness of said phosphorus doped oxide is approximately five thousand Ångstroms.

18. An apparatus for providing a uniform oxide layer over a metal layer in a semiconductor device, said apparatus comprising:

a semiconductor device comprising a metal layer;

a layer of a first doped oxide placed over said metal layer wherein said layer of said first doped oxide has a slow etch rate; and

a layer of a second doped oxide placed over said layer of said first doped oxide wherein said layer of said second doped oxide has a fast etch rate.

19. The apparatus as set forth in Claim 18 wherein said layer of said second doped oxide placed over said layer of said first doped oxide is etched through down to said layer of said first doped oxide.

20. The apparatus as set forth in Claim 19 wherein a thickness of said layer of said first doped oxide is approximately five thousand Ångstroms.

21. A method for providing a uniform oxide layer over a metal layer in a semiconductor device, said method comprising the steps of:

placing a layer of a first doped oxide over said metal layer wherein said first doped oxide has a slow etch rate;

placing a layer of a second doped oxide over said layer of said first doped oxide wherein said second doped oxide has a fast etch rate;

calculating a time period required for a wet etch process to etch through said layer of said second doped oxide; and

performing said wet etch process on said layer of said second doped oxide for said time period.

22. The method as set forth in Claim 21 wherein said metal layer in said semiconductor device is a metal link layer of a laser trimmed fuse.

23. The method as set forth in Claim 21 wherein said step of placing said layer of said first doped oxide over said metal layer comprises the step of:

forming said layer of said first doped oxide with a desired thickness.

24. The method as set forth in Claim 23 wherein said desired thickness of said layer of said first doped oxide is approximately five thousand Ångstroms.

25. The method as set forth in Claim 21 wherein said step of calculating said time period required for said wet etch process to etch through said layer of said second doped oxide comprises the step of:

dividing a thickness of said layer of said second doped oxide by a value of an etch rate of said wet etch process through said second doped oxide layer.